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Nota di contenuto	<p>Polar modulation and bipolar RF power devices,"E. -- A fully integrated 24 GHz fractional PLL with a low-power synchronized ring oscillator divider,"O. -- A 40GHz superheterodyne receiver integrated in 0.13/μm BiCMOS SiGe:C HBT technology,"S. -- A fully integrated 60 GHz LNA in SiGe:C BiCMOS technology,"Y. -- A 10 /μm thick RF-ID tag for chip-in-paper applications,"R. -- Offset voltage of Schottky-collector silicon-on-glass vertical PNP's,"G. -- Thin film magnetic materials for RFIC passives,"Y. -- Usage of HBTs beyond BV/sub CEO/,"J. -- Unified electro-thermal stability criterion for bipolar transistors,"T. -- Assessing reliability issues in cryogenically-operated SiGe HBTs,"Chendong -- Electrothermal stability of bipolar transistors at medium- and high-current operation regimes,"N. -- The effects of layout variation on the thermal characteristics of SiGe HBTs,"J. -- Statistical modeling of high-frequency bipolar transistors,"M. -- Study of bipolar transistor matching at high current level with various test configurations leading to a new model approach,"S. -- Improved vertical PNP collector-base breakdown using 2D Monte-Carlo TCAD simulations,"A. -- BSCR ESD protection in 250V process taking into account the turn-off effect,"V. -- New lateral DMOS and IGBT structures realized on a partial SOI substrate based on LEGO process,"I. -- High-voltage semiconductor devices: status and trends,"G. -- A 43-45Gb/s 2.5V integrated clock and data recovery circuit in SiGe using low-voltage topologies,"D. -- NOR/OR register based ECL circuits for maximum data rate,"H. -- A 10Gb/s injection-locked clock recovery circuit in 47GHz f/sub T/ SiGe BiCMOS,"Jing-Hong -- Notice of</p>

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